Amendments to the Specification

Please replace the paragraph beginning on page 1, line 13 with the following amended paragraph:

In the case of forming an element on a conventional semiconductor substrate, a wiring thin film deposition method as shown in ~~Fig. 3~~ Figs. 1-3 is carried out. First of all, an insulating film 2 (for example, SiO_2 BPSG) is deposited on a semiconductor substrate 1 typically of a material such as silicon, and a barrier layer 3 (for example, Ti, TiN or a laminate of the two) is deposited. Next, an Al film is deposited with the semiconductor substrate heated to 150 - 400°C, by a sputtering method using an Al-Si-Cu target having Si added to 0.05 – 1.0% which is at least the solution limit of Al.

Please replace the paragraph beginning on page 6, line 10 with the following amended paragraph:

A third embodiment of the present invention will now be described using Fig. 11, Fig. 12 and Fig. 13. First of all, an insulating film 41 (for example SiO_2, BPSG) is deposited on a semiconductor substrate 40. Next, a Ti film 42 is deposited to a thickness of 50 nm, as a barrier layer. The film formation conditions up to the barrier layer can be the same as in the related art. With this embodiment, before deposition of Al, an Al_3Ti film 43 is previously deposited to a thickness of 10 – 20 nm by a sputter method using an Al_3Ti target. An Al film [[43]] 44 is then deposited to a thickness of 400 – 800 nm at a deposition temperature of at least 400°C by a sputter method using

an Al–1.0% Si-0.5% Cu target. The reason for making the deposition temperature of the Al film at least 400°C is to promote absorption of Si into the Al_3Ti. After that, a TiN film is deposited to a thickness of 50 nm as an anti-reflection film.

Please replace the paragraph beginning on page 7, line 25 with the following amended paragraph:

A fifth embodiment of the present invention will now be described using Fig. 16 and Fig. 17. First of all, an insulating film 61 (for example SiO2, BPSG) is deposited on a semiconductor substrate 60. Then, a Ti film 62 is deposited as a barrier layer. Next, an Al film [[62]] 63 is deposited on the ~~insulating film~~ barrier layer 62 by a sputter method using an Al-0.8%Si-0.3%Cu target. The film formation conditions up to the Al film can be the same as in the related art. With this embodiment, after deposition of Al, an Al_3Ti film 64 is previously deposited to a thickness of 10 – 20 nm by a sputter method using an Al_3Ti target. After that a TiN anti-reflection film is deposited to a thickness of approximately 50nm in the same way as in the related art. After deposition of the antireflection film has been completed, annealing is carried out at a high temperature of at least 400°C in order to promote absorption of Si into the Al_3Ti film.